

Features:

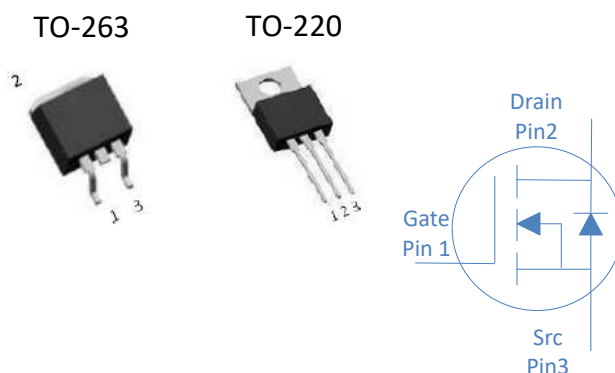
- ◇ High Speed Power Switching
- ◇ Enhanced Body diode dv/dt capability
- ◇ Enhanced Avalanche Ruggedness
- ◇ 100% UIS Tested, 100% Rg Tested
- ◇ Lead Free, Halogen Free

Application:

- ◇ Synchronous Rectification in SMPS ◇
- Hard Switching and High Speed Circuit ◇
- DC/DC in Telecoms and Industrial

40V N-Ch Power MOSFET

V_{DS}		40	V
$R_{DS(on),typ}$	TO-263	1.9	mΩ
$R_{DS(on),typ}$	TO-220	2.2	mΩ
I_D (Silicon Limited)		182	A
I_D (Package Limited)		120	A



Part Number	Package	Marking
KUGB019N04A	TO-263	GB019N04A
KEGP019N04A	TO-220	GP019N04A

Absolute Maximum Ratings at $T_J=25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current(Silicon Limited)	I_D	$T_C=25^\circ\text{C}$	182	A
		$T_C=100^\circ\text{C}$	129	
		$T_C=25^\circ\text{C}$	120	
Continuous Drain Current(Package Limited)		$T_C=25^\circ\text{C}$	120	
Drain to Source Voltage	V_{DS}	-	40	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	590	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.1\text{mH}$, $T_C=25^\circ\text{C}$	180	mJ
Power Dissipation	P_D	$T_C=25^\circ\text{C}$	150	W
Operating and Storage Temperature	T_J , T_{stg}	-	-55 to 175	$^\circ\text{C}$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	60	$^\circ\text{C/W}$
Thermal Resistance Junction-Case	$R_{\theta JC}$	1	$^\circ\text{C/W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	3.2	4.0	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=40V, T_j=25^\circ\text{C}$	-	-	1	μA
		$V_{GS}=0V, V_{DS}=40V, T_j=100^\circ\text{C}$	-	-	100	
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$ TO-263	-	1.9	2.3	$m\Omega$
Drain to Source on Resistance		$V_{GS}=10V, I_D=20A$ TO-220	-	2.2	2.6	$m\Omega$
Transconductance	g_{fs}	$V_{DS}=5V, I_D=20A$	-	75	-	S
Gate Resistance	R_G	$V_{GS}=0V, V_{DS}$ Open, $f=1\text{MHz}$	-	0.8	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=20V, f=1\text{MHz}$	-	4982	-	pF
Output Capacitance	C_{oss}		-	906	-	
Reverse Transfer Capacitance	C_{rss}		-	98	-	
Total Gate Charge	$Q_g(10V)$	$V_{DD}=20V, I_D=20A, V_{GS}=10V$	-	72	-	nC
Gate to Source Charge	Q_{gs}		-	20	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	15	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=20A, V_{GS}=10V, R_G=10\Omega,$	-	21	-	ns
Rise time	t_r		-	11	-	
Turn off Delay Time	$t_{d(off)}$		-	29	-	
Fall Time	t_f		-	8	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R=20V, I_F=20A, dI_F/dt=100A/\mu s$	-	41	-	ns
Reverse Recovery Charge	Q_{rr}		-	41	-	nC

Fig 1. Typical Output Characteristics

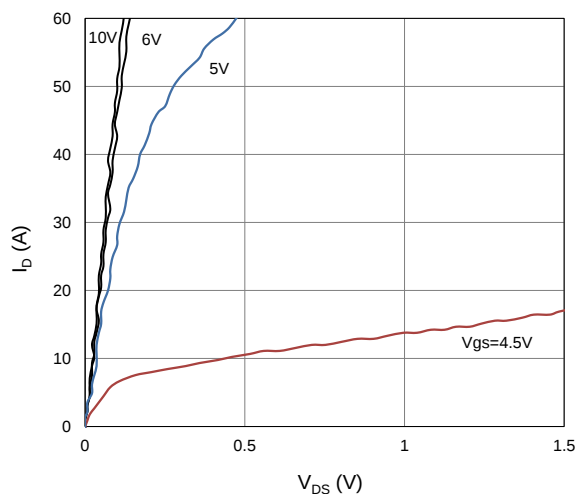


Figure 2. On-Resistance vs. Gate-Source Voltage

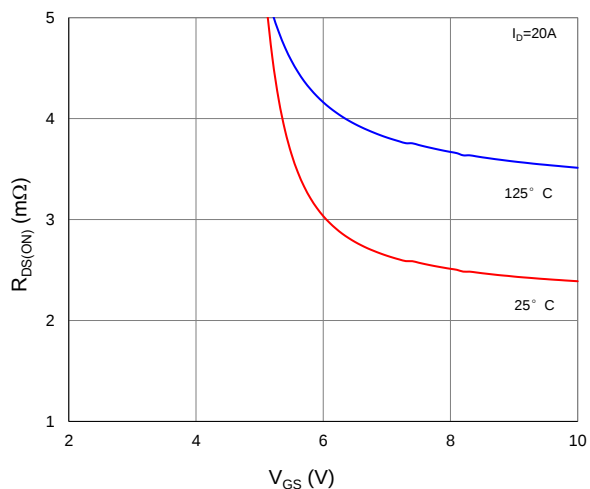


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

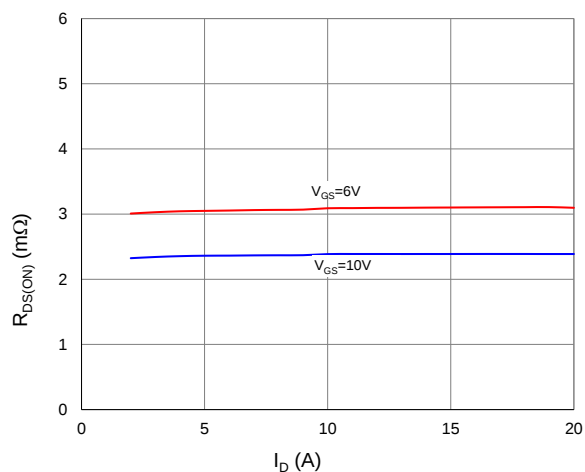


Figure 4. Normalized On-Resistance vs. Junction Temperature

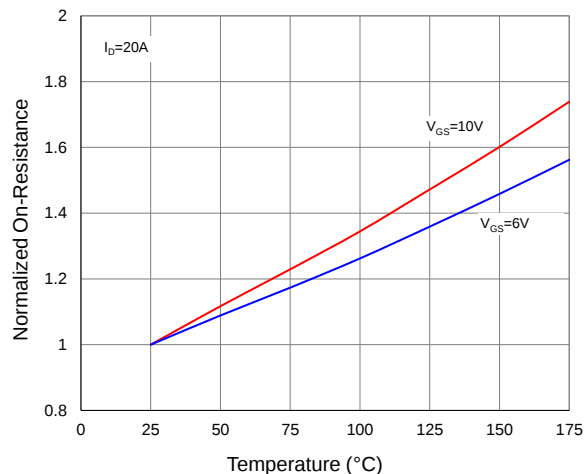


Figure 5. Typical Transfer Characteristics

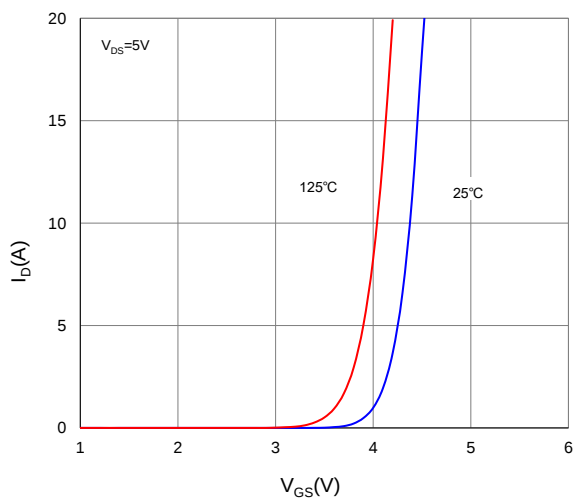


Figure 6. Typical Source-Drain Diode Forward Voltage

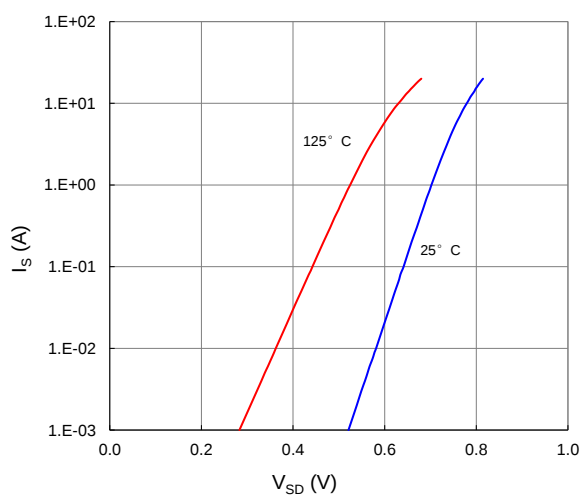


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

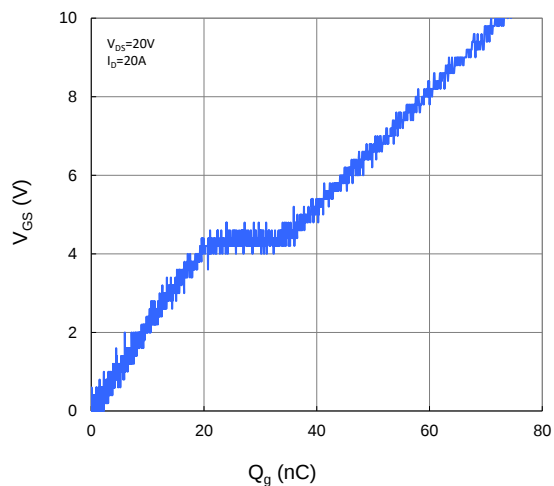


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

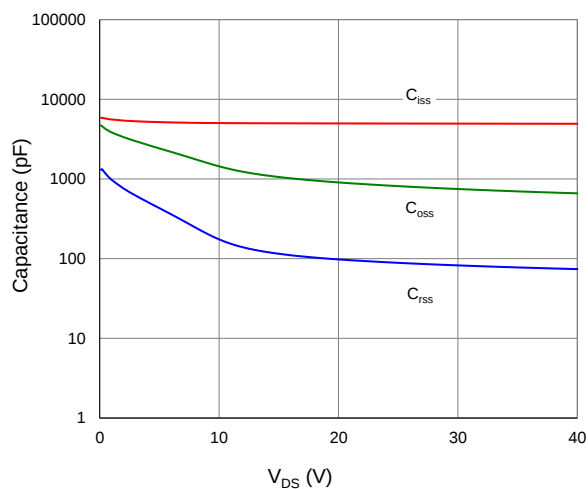


Figure 9. Maximum Safe Operating Area

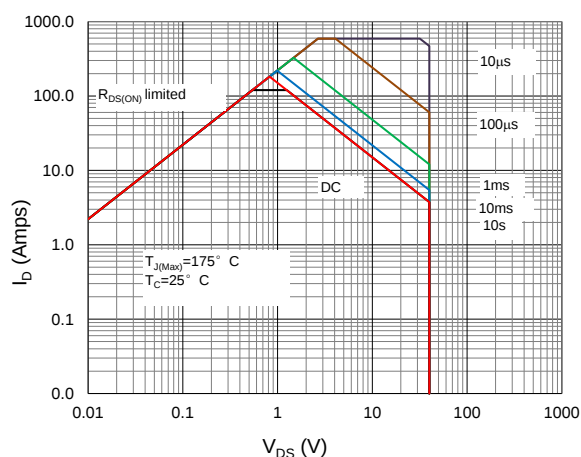


Figure 10. Maximum Drain Current vs. Case Temperature

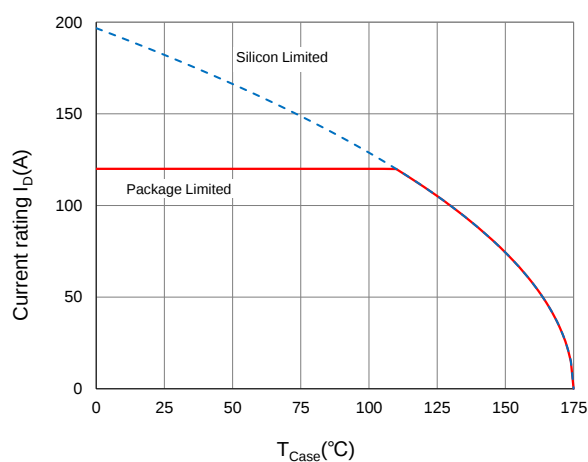
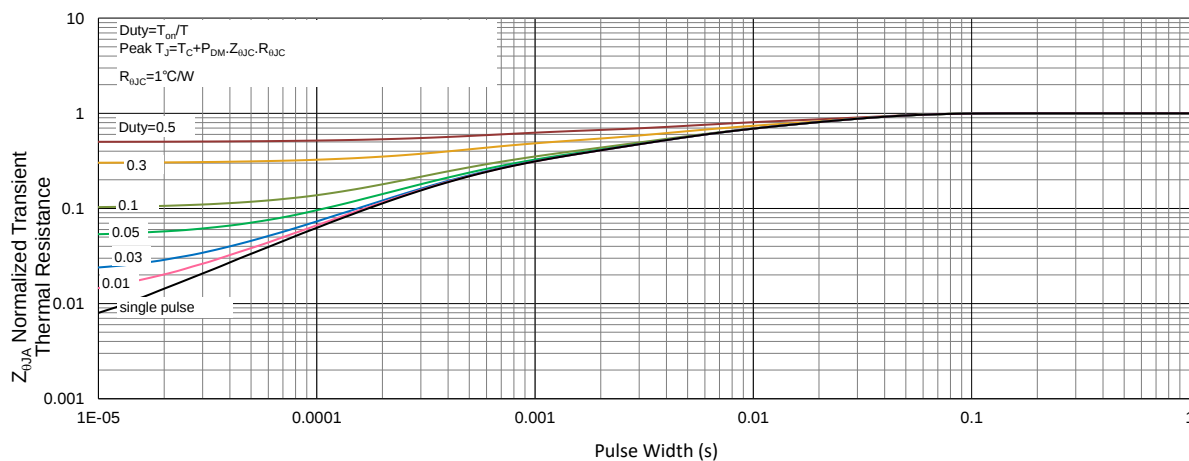
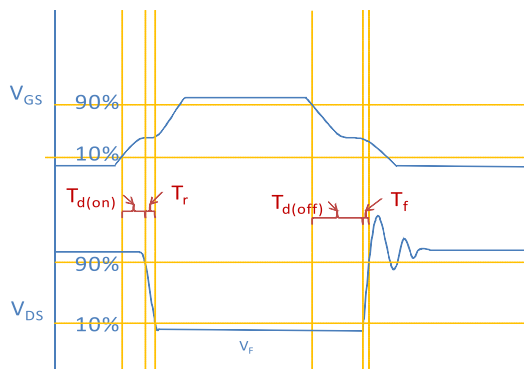
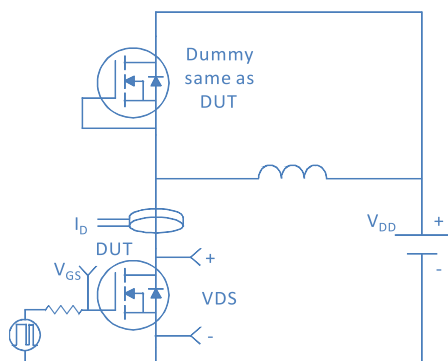


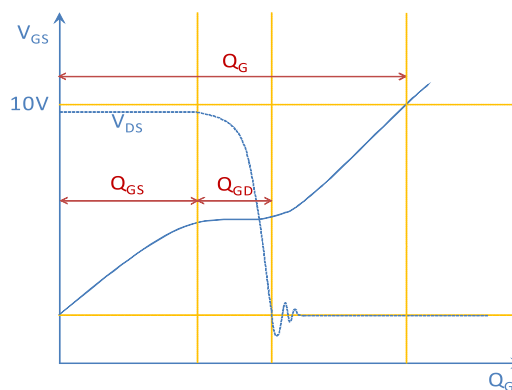
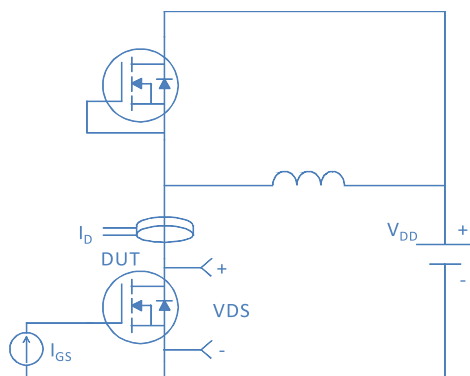
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



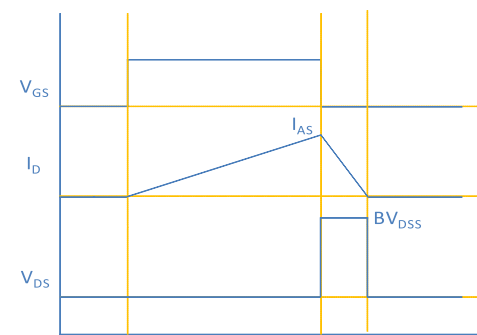
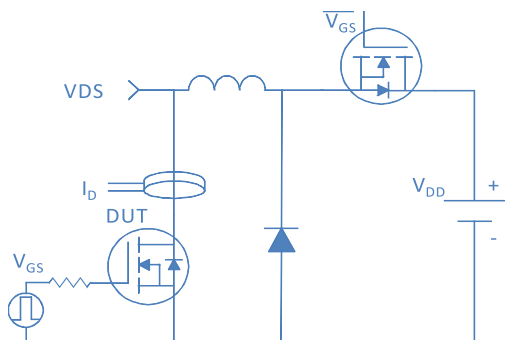
Inductive switching Test



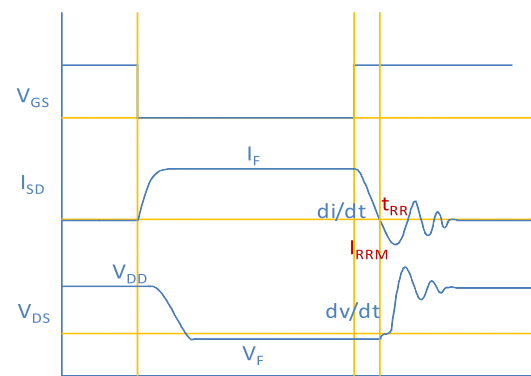
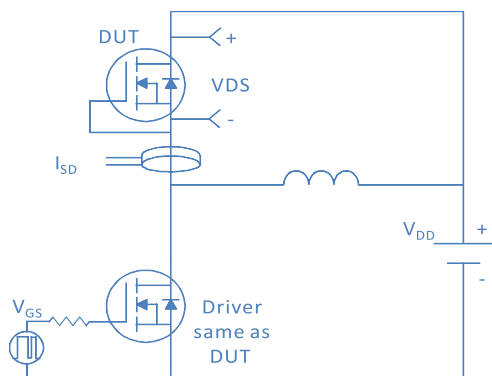
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

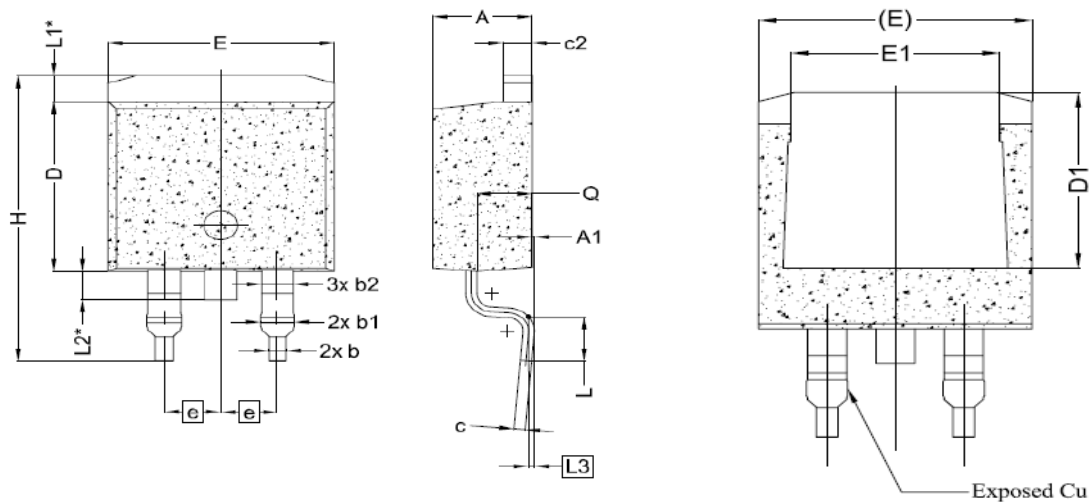


Diode Recovery Test



Package Outline

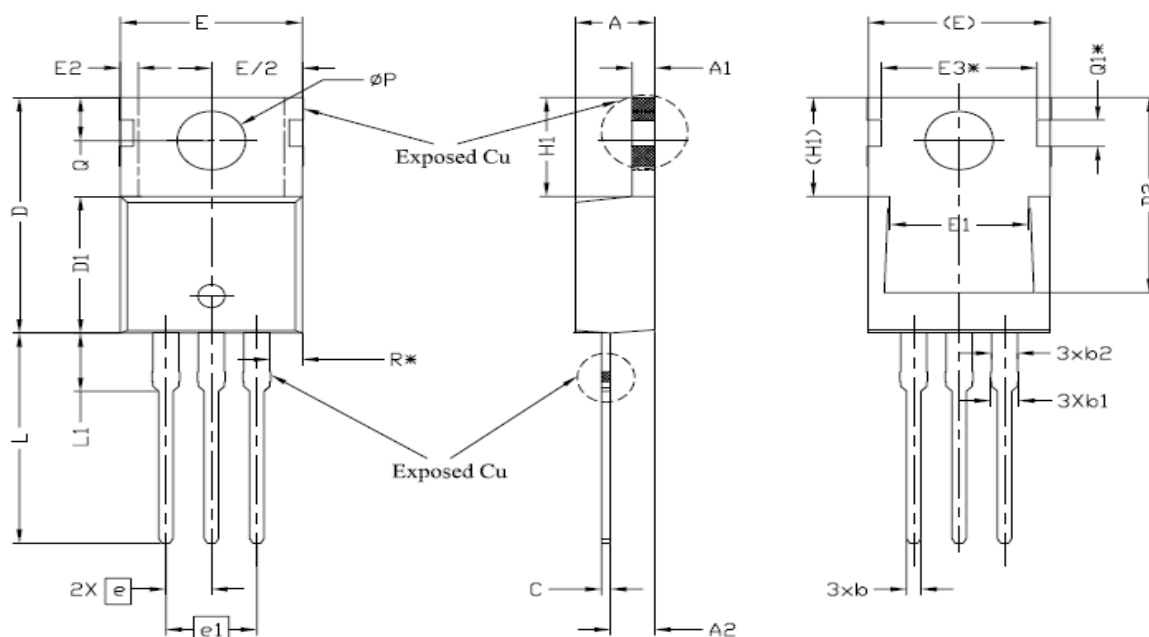
TO-263, 2 leads



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

Package Outline

TO-220, 3 leads



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.24	4.44	4.64	
A1	1.15	1.27	1.40	
A2	2.30	2.48	2.70	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
c	0.40	0.50	0.60	
D	14.70	15.37	16.00	4
D1	8.82	8.92	9.02	
D2	12.63	12.73	12.83	5
E	9.96	10.16	10.36	4,5
E1	6.86	7.77	8.89	5
E2	-	-	0.76	6
E3*	8.70REF.			
e	2.54BSC			
e1	5.08BSC			
H1	6.30	6.45	6.60	5,6
L	13.47	13.72	13.97	
L1	3.60	3.80	4.00	
ØP	3.75	3.84	3.93	
Q	2.60	2.80	3.00	
Q1*	1.73REF.			
R*	1.62REF.			